

37 CFR 1.501 INFORMATION DISCLOSURE STATEMENT IN A PATENT (use several sheets if necessary)					Docket No. 09792909-5625	Serial No.		
					Applicants: Osamu Goto, et al.			
					Filing Date June 25, 2003	Group Art Unit		
U.S. PATENT DOCUMENTS								
Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If appropriate	
ON	AA	6,060,335	5-9-00	Rennie				
	AB							
	AC							
	AD							
	AE							
	AF							
	AG							
FOREIGN PATENT DOCUMENTS							Translation	
		Document Number	Date	Country	Class	Subclass	Yes	No
ON	AH	JP11-54794	2-26-99	Japan			Abstract	
ON	AI	JP09-266326	10-7-97	Japan			Abstract	
ON	AJ	JP11-243251	9-7-99	Japan			Abstract	
ON	AK	EP 0 803 916	10-29-99	Europe				
	AL							
	AM							
	AN							
	AO							
	AP							
	AQ							
	AR							
	AS							
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)								
ON	AT	Shuji Nakamura, et al., "Characteristics of InGaN multi-quantum-well-structure laser diodes", Applied Physics Letters, 1996, Vol. 68, No. 23, pp. 3269-3271						
	AU							
	AV							
	AW							
	AX							
	AY							
	AZ							
Examiner		ON	Date Considered		9/21/04			
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								